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TI, Ramtron move on 130-nm FRAM manufacturing

ElectronicNews


By Colleen Taylor

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Texas Instruments (TI) and nonvolatile ferroelectric random access memory (FRAM) supplier **Ramtron International Corp.** reported Monday they have reached what they called "a significant milestone" in the development of FRAM technology that has resulted in a commercial manufacturing agreement for FRAM memory products.

The companies said the agreement provides for the production of **Ramtron's** FRAM memory products on TI's 130-nm FRAM manufacturing process, including **Ramtron's** new 4-Mb FRAM memory. **Ramtron** and TI have been [working together](#) since August 2001, when they entered into a FRAM licensing and development agreement.

"This manufacturing agreement marks a major leap forward in the commercialization of higher-density FRAM products," **Ramtron** CEO Bill Staunton said in a statement. "In addition to a 4-Mb device, we are planning to sample at least one additional product off of the TI line in 2007," he added.

To create the embedded FRAM module, TI said it added two additional mask steps to its standard, 130-nm copper-interconnect process. By moving to a 130-nm process, the companies will deliver **Ramtron's** 4-Mb FRAM memories using what they claimed are the smallest commercial FRAM cells shown-to-date and enabling a higher memory density than that achieved with SRAM cells. To achieve this cell size, the process features a capacitor-over-plug process that places the nonvolatile capacitor stack directly on top of the W-plug transistor contact.

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